

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

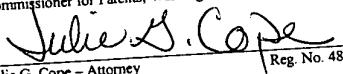
Application of

Applicant : David L. Chapek
Serial No. : 09/605,293
Filed : June 28, 2000
Title : SEMICONDUCTOR DEVICES INCLUDING A LAYER OF
POLYCRYSTALLINE SILICON HAVING A SMOOTH MORPHOLOGY
Docket : MIO 0037 VA
Art Unit : 2811

Assistant Commissioner for Patents
Washington, DC 20231

2811
#5/AMO/B
1/2/01

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CERTIFICATE OF MAILING	
I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on November 15, 2001.	
	Reg. No. 48,624
Julie G. Cope - Attorney	

Sir:

AMENDMENT

This paper is being filed in response to the Office Action mailed on October 2, 2001. Reconsideration is respectfully requested in light of the remarks below.

CLEAN VERSION OF THE AMENDMENTS

(A version of these amendments with markings to show the changes is attached to this paper as a separate appendix.)

IN THE CLAIMS

Model ~~9. (Amended) A semiconductor device precursor comprising:~~
~~a semiconductor substrate;~~

B ~~a layer of silicon dioxide formed on said semiconductor substrate, said layer of
 silicon dioxide having been doped with hydrogen ions deposited by a plasma source ion
 implantation process, wherein said layer of silicon dioxide is free of metal contaminants;
 and~~

Model ~~a layer of polycrystalline silicon formed on said layer of silicon dioxide, said layer
 of polycrystalline silicon having a smooth morphology.~~

Model ~~10. (Amended) A field effect transistor comprising:~~